

DB3Y501KEL

Schottky Barrier Diode DB3Y501KEL

Silicon epitaxial planar type

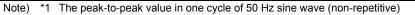
For high speed switching circuits DB3X501K in NMini3 type package

## Features

- Short reverse recovery time trr
- Low terminal capacitance Ct
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol :4H
- Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C								
Parameter	Symbol	Rating	Unit					
Reverse voltage	VR	50	V					
Repctitive peak reverse voltage	VRRM	50	V					
Forward current (Average)	IF (AV)	200	mA					
Peak forward current	IFM	300	mA					
Non-repetitive peak forward surge current *1	IFSM	1	А					
Junction temperature	Tj	125	С°					
Operating ambient temperature	Topr	-40 to +85	С°					
Storage temperature	Tstg	-55 to +125	°C					
Note) *1. The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)								



## ■ Electrical Characteristics Ta = 25 °C ± 3 °C

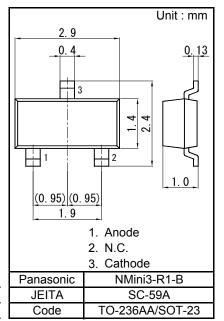
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF1	IF = 30 mA			0.36	V
	VF2	IF = 200 mA			0.55	V
Reverse current	IR	VR = 50 V			200	μA
Terminal capacitance	Ct	VR = 10 V, f = 1 MHz		4.0		pF
Reverse recovery time <sup>*1</sup>	trr	IF = IR = 100 mA, Irr = 0.1 × IR		1.6		
	ul	RL = 100 Ω	1.0		ns	

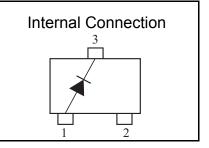
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

- 3. Absolute frequency of input and output is 1000 MHz.
- 4. \*1 trr measurement circuit Bias Insertion Unit Output Pulse Input Pulse (N-50BU) tp 10% ſ <u>↓</u>90% ٧<sub>R</sub>  $I_{rr} = 0.1 \times IR$  $t_p = 2 \mu s$  $t_r = 0.35 ns$ I<sub>F</sub> = 100 mA Wave Form Analyzer Pulse Generator I<sub>R</sub> = 100 mA (PG-10N) (SAS-8130) R<sub>L</sub> = 100 Ω  $\delta = 0.05$ R<sub>S</sub> = 50 Ω R<sub>i</sub> = 50 Ω

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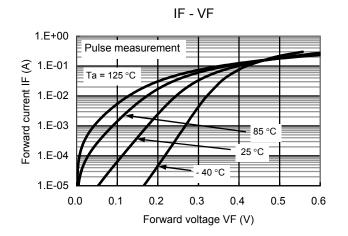


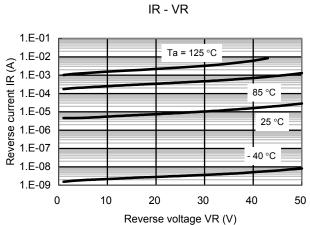




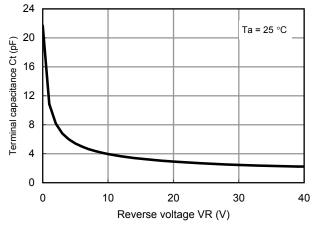
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## Technical Data (reference)





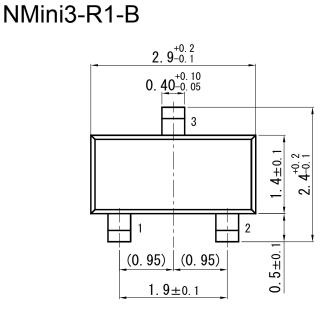


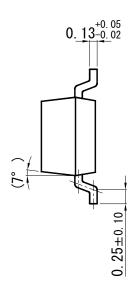


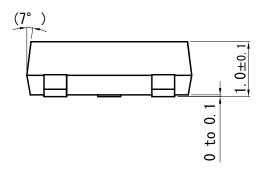


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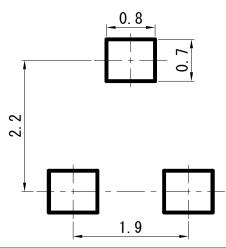
Unit : mm







■ Land Pattern (Reference) (Unit : mm)



Established : 2013-04-27 Revised : ####-##-##

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